

DATA SHEET

BFG31

PNP 5 GHz wideband transistor

Product specification
Supersedes data of November 1992

1995 Sep 12



PNP 5 GHz wideband transistor

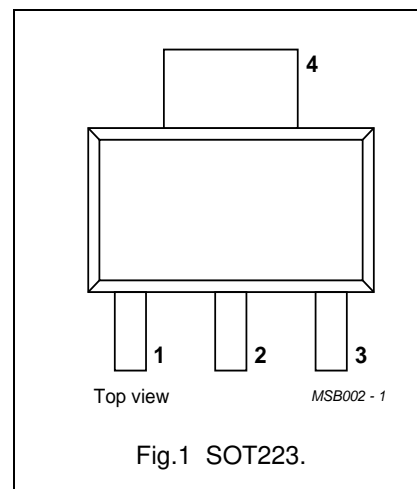
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FEATURES

- High output voltage capability
- High gain bandwidth product
- Good thermal stability
- Gold metallization ensures excellent reliability.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	emitter
4	collector



DESCRIPTION

PNP planar epitaxial transistor mounted in a plastic SOT223 envelope.

It is intended for wideband amplifier applications.

NPN complement is the BFG97.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CEO}	collector-emitter voltage	open base	—	—	–15	V
I_C	DC collector current		—	—	–100	mA
P_{tot}	total power dissipation	up to $T_s = 135\text{ °C}$; note 1	—	—	1	W
h_{FE}	DC current gain	$I_C = -70\text{ mA}$; $V_{CE} = -10\text{ V}$; $T_{amb} = 25\text{ °C}$	25	—	—	
f_T	transition frequency	$I_C = -70\text{ mA}$; $V_{CE} = -10\text{ V}$; $f = 500\text{ MHz}$; $T_{amb} = 25\text{ °C}$	—	5.0	—	GHz
G_{UM}	maximum unilateral power gain	$I_C = -70\text{ mA}$; $V_{CE} = -10\text{ V}$; $f = 800\text{ MHz}$; $T_{amb} = 25\text{ °C}$	—	12	—	dB
V_o	output voltage	$I_C = -100\text{ mA}$; $V_{CE} = -10\text{ V}$; $R_L = 75\text{ }\Omega$; $T_{amb} = 25\text{ °C}$	—	600	—	mV

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	–20	V
V_{CEO}	collector-emitter voltage	open base	—	–15	V
V_{EBO}	emitter-base voltage	open collector	—	–3	V
I_C	DC collector current		—	–100	mA
P_{tot}	total power dissipation	up to $T_s = 135\text{ °C}$; note 1	—	1	W
T_{stg}	storage temperature		–65	150	°C
T_j	junction temperature		—	175	°C

Note

1. T_s is the temperature at the soldering point of the collector tab.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	THERMAL RESISTANCE
$R_{th\ j-s}$	thermal resistance from junction to soldering point	up to $T_s = 135\text{ °C}$; note 1	40 K/W

Note

- T_s is the temperature at the soldering point of the collector tab.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

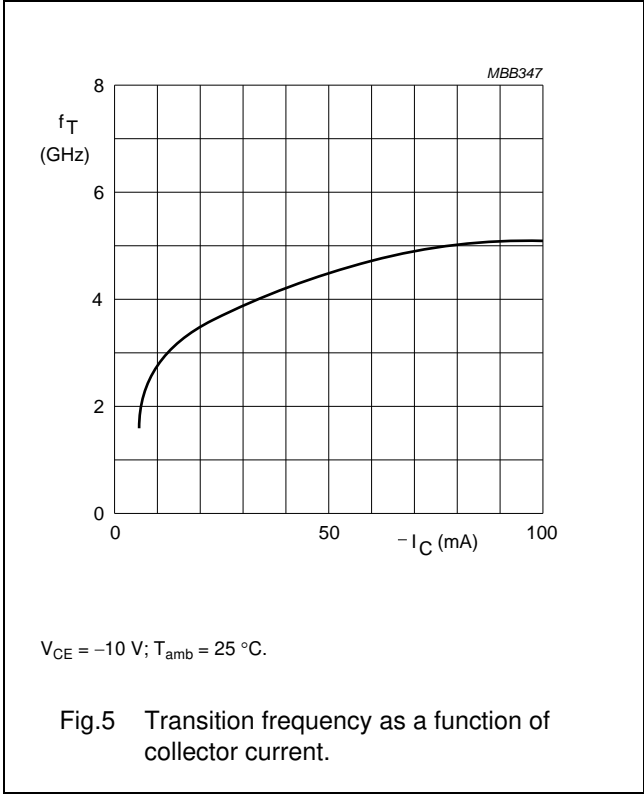
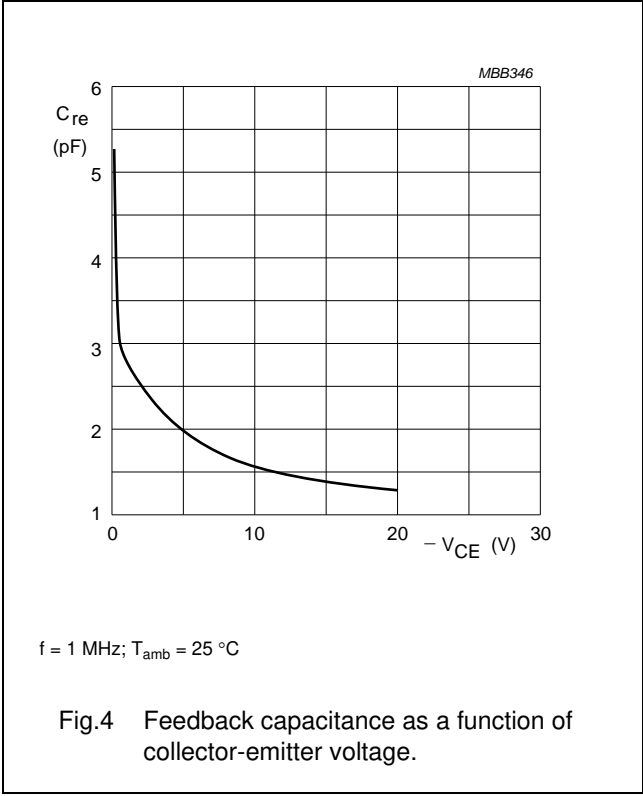
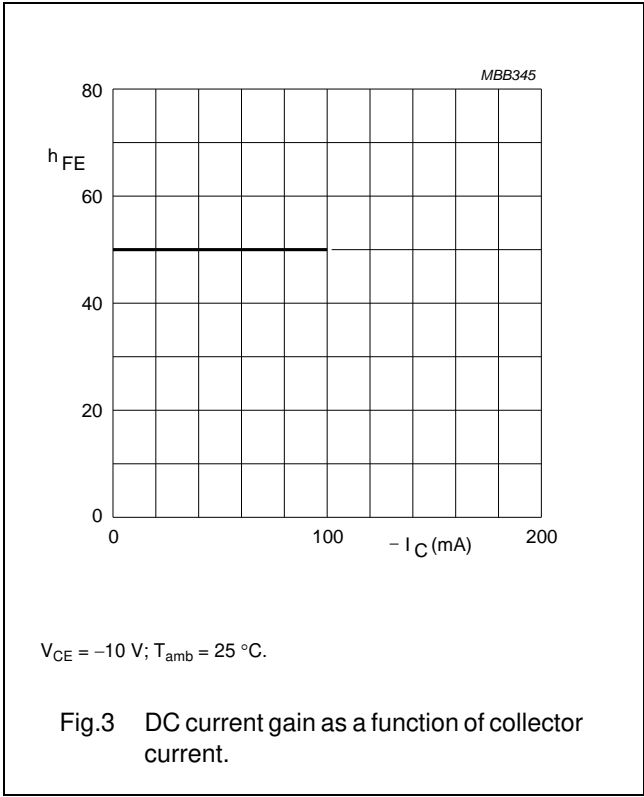
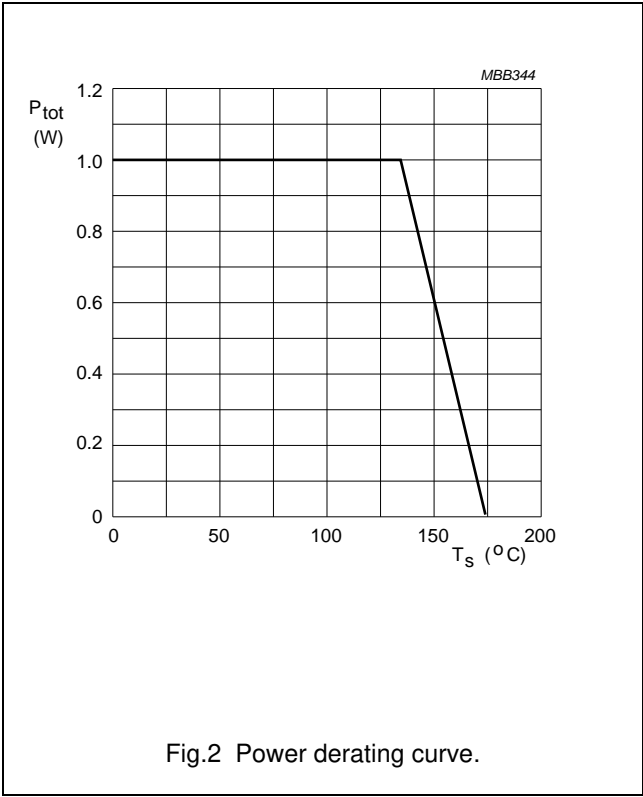
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	open emitter; $I_C = -10\text{ mA}$	-20	—	—	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	open base; $I_C = -10\text{ mA}$	-18	—	—	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	open collector; $I_E = -0.1\text{ mA}$	-3	—	—	V
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = -10\text{ V}$	—	—	-1	μA
h_{FE}	DC current gain	$I_C = -70\text{ mA}$; $V_{CE} = -10\text{ V}$; $T_{amb} = 25\text{ °C}$	25	—	—	
C_{cb}	collector-base capacitance	$I_C = 0$; $V_{CB} = -10\text{ V}$; $f = 1\text{ MHz}$	—	1.8	—	pF
C_{eb}	emitter-base capacitance	$I_C = 0$; $V_{EB} = -10\text{ V}$; $f = 1\text{ MHz}$	—	5	—	pF
C_{re}	feedback capacitance	$I_C = 0$; $V_{CE} = -10\text{ V}$; $f = 1\text{ MHz}$; $T_{amb} = 25\text{ °C}$	—	1.6	—	pF
f_T	transition frequency	$I_C = -70\text{ mA}$; $V_{CE} = -10\text{ V}$; $f = 500\text{ MHz}$; $T_{amb} = 25\text{ °C}$	—	5	—	GHz
G_{UM}	maximum unilateral power gain; note 1	$I_C = -70\text{ mA}$; $V_{CE} = -10\text{ V}$; $f = 500\text{ MHz}$; $T_{amb} = 25\text{ °C}$	—	16	—	dB
		$I_C = -70\text{ mA}$; $V_{CE} = -10\text{ V}$; $f = 800\text{ MHz}$; $T_{amb} = 25\text{ °C}$	—	12	—	dB
V_o	output voltage	note 2	—	600	—	mV
V_o	output voltage	note 3	—	550	—	mV

Notes

- G_{UM} is the maximum unilateral power gain, assuming S_{12} is zero and $G_{UM} = 10 \log \frac{|s_{21}|^2}{(1 - |s_{11}|^2)(1 - |s_{22}|^2)}$ dB.
- $d_{im} = -60\text{ dB}$; $I_C = -70\text{ mA}$; $V_{CE} = -10\text{ V}$; $R_L = 75\text{ }\Omega$; $T_{amb} = 25\text{ °C}$;
 $V_p = V_o$ at $d_{im} = -60\text{ dB}$; $f_p = 850.25\text{ MHz}$;
 $V_q = V_o - 6\text{ dB}$; $f_q = 858.25\text{ MHz}$;
 $V_r = V_o - 6\text{ dB}$; $f_r = 860.25\text{ MHz}$;
measured at $f_{(p+q-r)} = 848.25\text{ MHz}$.
- $d_{im} = -60\text{ dB}$ (DIN 45004B); $I_C = -70\text{ mA}$; $V_{CE} = -10\text{ V}$; $R_L = 75\text{ }\Omega$; $T_{amb} = 25\text{ °C}$;
 $V_p = V_o$ at $d_{im} = -60\text{ dB}$; $f_p = 445.25\text{ MHz}$;
 $V_q = V_o - 6\text{ dB}$; $f_q = 453.25\text{ MHz}$;
 $V_r = V_o - 6\text{ dB}$; $f_r = 455.25\text{ MHz}$;
measured at $f_{(p+q-r)} = 443.25\text{ MHz}$.

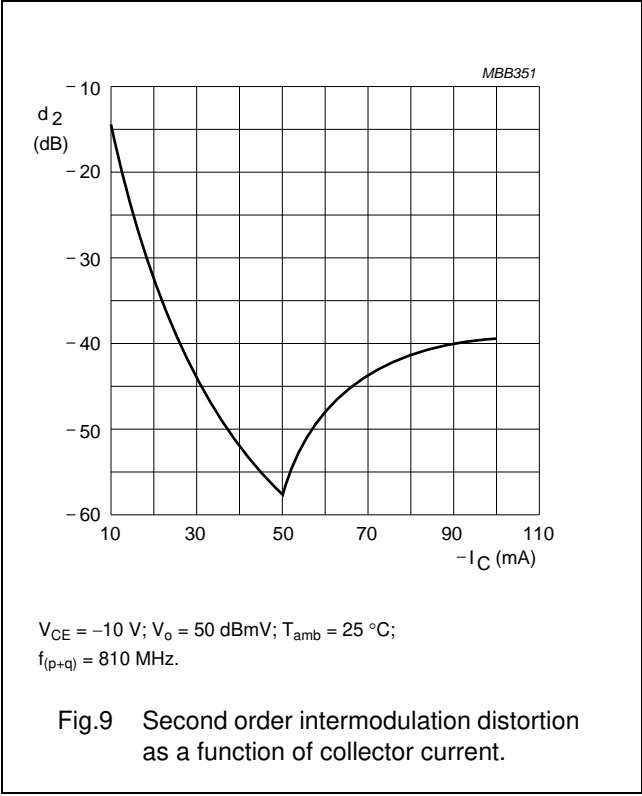
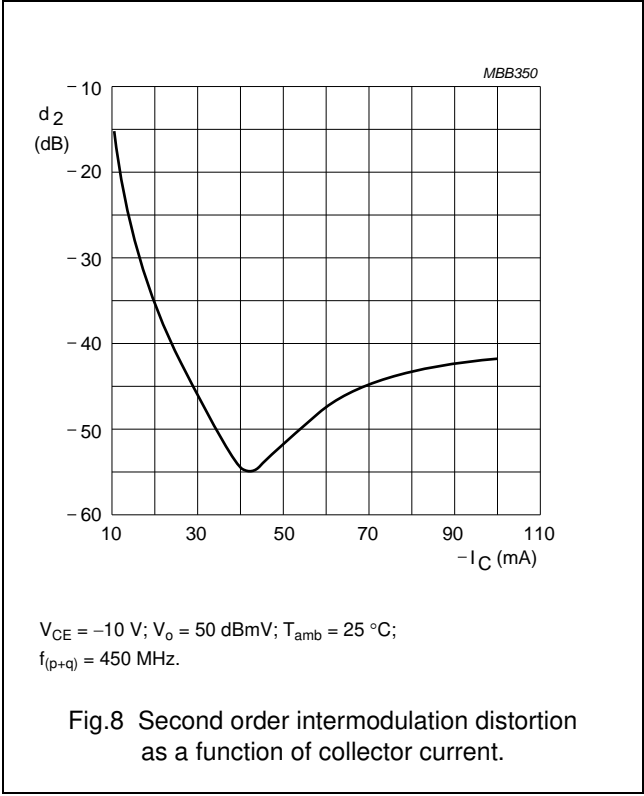
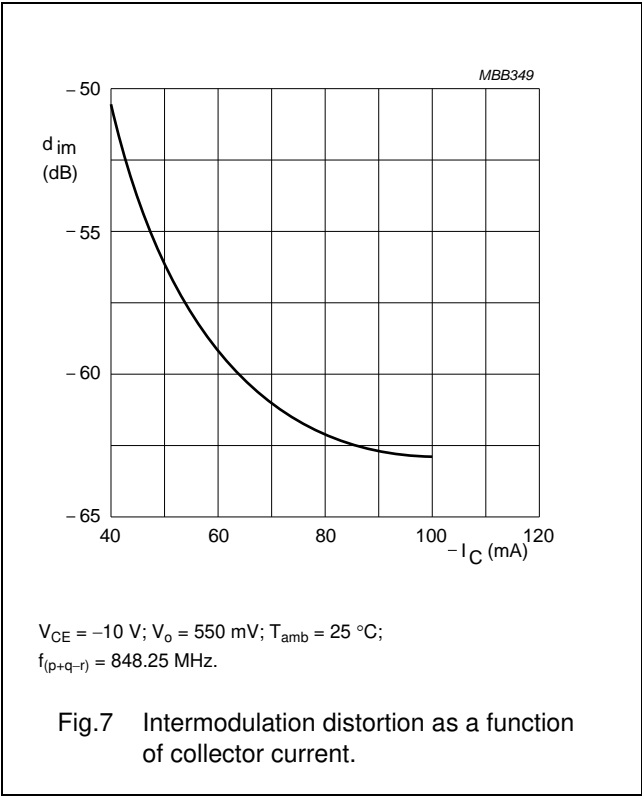
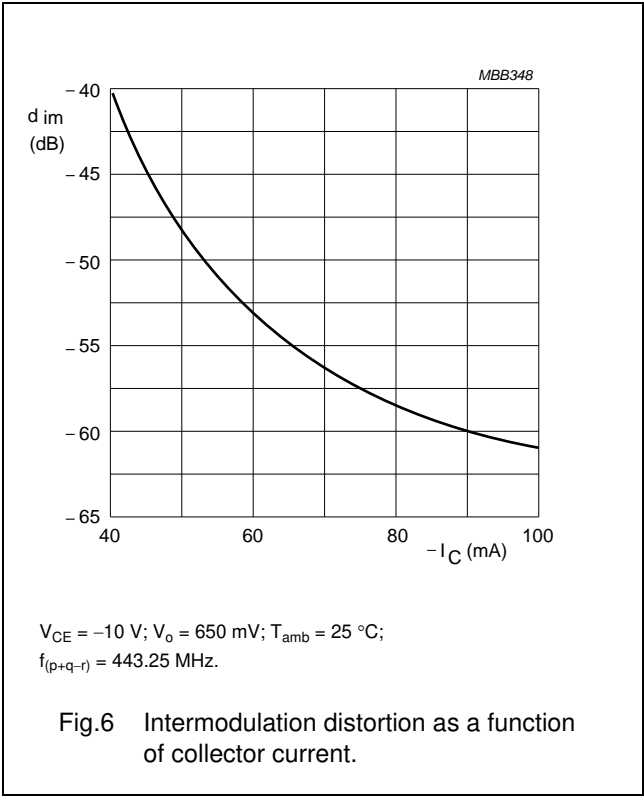
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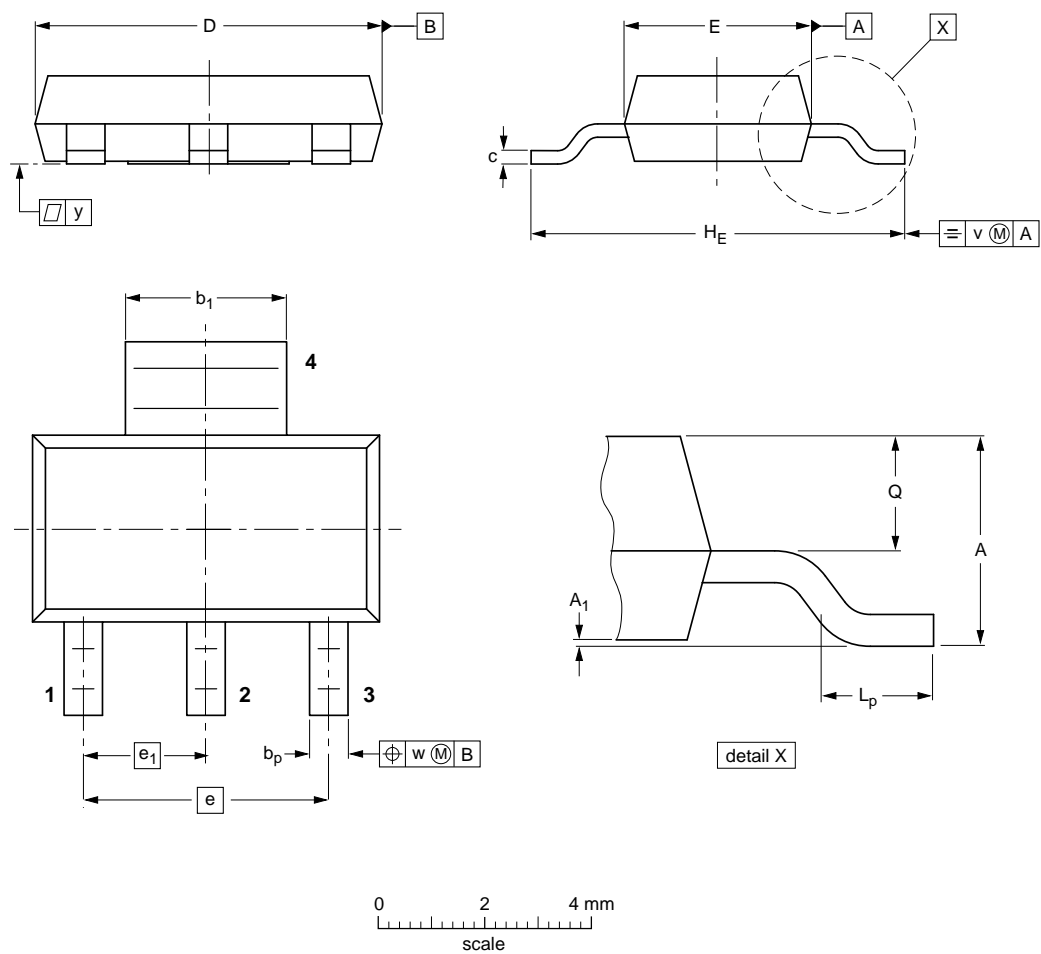
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PACKAGE OUTLINE

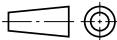
Plastic surface-mounted package with increased heatsink; 4 leads

SOT223



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b _p	b ₁	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT223			SC-73			04-11-10 06-03-16

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Contact information

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